

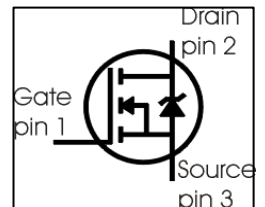
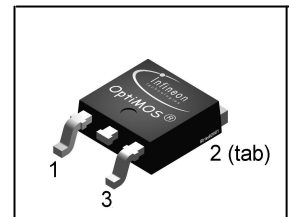
**OptiMOS® Power-Transistor**
**Feature**

- N-Channel
- Enhancement mode
- Logic Level
- 175°C operating temperature
- Avalanche rated
- $dv/dt$  rated

**Product Summary**

|              |    |    |
|--------------|----|----|
| $V_{DS}$     | 75 | V  |
| $R_{DS(on)}$ | 50 | mΩ |
| $I_D$        | 25 | A  |

P- TO252 -3-11



| Type           | Package        | Ordering Code | Marking |
|----------------|----------------|---------------|---------|
| SPD22N08S2L-50 | P- TO252 -3-11 | Q67060-S6062  | 2N08L50 |

**Maximum Ratings**, at  $T_j = 25\text{ °C}$ , unless otherwise specified

| Parameter   | Symbol              | Value       | Unit              |
|---|---------------------|-------------|-------------------|
| Continuous drain current<br>$T_C=22\text{°C}$   | $I_D$               | 25<br>18    | A                 |
| Pulsed drain current<br>$T_C=25\text{°C}$   | $I_{D\text{ puls}}$ | 100         |                   |
| Avalanche energy, single pulse<br>$I_D=22\text{A}$ , $V_{DD}=25\text{V}$ , $R_{GS}=25\text{Ω}$                              | $E_{AS}$            | 94          | mJ                |
| Repetitive avalanche energy, limited by $T_{jmax}^{1)}$   | $E_{AR}$            | 7.5         |                   |
| Reverse diode $dv/dt$<br>$I_S=22\text{A}$ , $V_{DS}=60\text{V}$ , $di/dt=200\text{A}/\mu\text{s}$ , $T_{jmax}=175\text{°C}$ | $dv/dt$             | 6           | kV/ $\mu\text{s}$ |
| Gate source voltage   | $V_{GS}$            | $\pm 20$    | V                 |
| Power dissipation<br>$T_C=25\text{°C}$  | $P_{tot}$           | 75          | W                 |
| Operating and storage temperature   | $T_j, T_{stg}$      | -55... +175 | °C                |
| IEC climatic category; DIN IEC 68-1   |                     | 55/175/56   |                   |

**Thermal Characteristics**

| Parameter                                      | Symbol     | Values |      |      | Unit |
|--|------------|--------|------|------|------|
|  |            | min.   | typ. | max. |      |
| Characteristics                                |            |        |      |      |      |
| Thermal resistance, junction - case            | $R_{thJC}$ | -      | 1.34 | 2    | K/W  |
| Thermal resistance, junction - ambient, leaded | $R_{thJA}$ | -      | -    | 100  |      |
| SMD version, device on PCB:                    | $R_{thJA}$ |        |      |      |      |
| @ min. footprint                               |            | -      | -    | 75   |      |
| @ 6 cm <sup>2</sup> cooling area <sup>2)</sup> |            | -      | -    | 50   |      |

**Electrical Characteristics, at  $T_j = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified**

| Parameter  | Symbol        | Values |           |          | Unit       |
|--|---------------|--------|-----------|----------|------------|
|  |               | min.   | typ.      | max.     |            |
| Static Characteristics   |               |        |           |          |            |
| Drain-source breakdown voltage<br>$V_{GS}=0V, I_D=1mA$   | $V_{(BR)DSS}$ | 75     | -         | -        | V          |
| Gate threshold voltage, $V_{GS} = V_{DS}$<br>$I_D=31\mu A$   | $V_{GS(th)}$  | 1.2    | 1.6       | 2        |            |
| Zero gate voltage drain current<br>$V_{DS}=75V, V_{GS}=0V, T_j=25^{\circ}C$<br>$V_{DS}=75V, V_{GS}=0V, T_j=125^{\circ}C$ | $I_{DSS}$     | -<br>- | 0.01<br>1 | 1<br>100 | $\mu A$    |
| Gate-source leakage current<br>$V_{GS}=20V, V_{DS}=0V$   | $I_{GSS}$     | -      | 1         | 100      |            |
| Drain-source on-state resistance<br>$V_{GS}=4.5V, I_D=11A$   | $R_{DS(on)}$  | -      | 48        | 65       | m $\Omega$ |
| Drain-source on-state resistance<br>$V_{GS}=10V, I_D=11A$  | $R_{DS(on)}$  | -      | 38        | 50       |            |

<sup>1</sup>Defined by design. Not subject to production test.

<sup>2</sup>Device on 40mm\*40mm\*1.5mm epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70  $\mu m$  thick) copper area for drain connection. PCB is vertical without blown air.

**Electrical Characteristics**

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Dynamic Characteristics**

|                              |              |   |    |     |     |    |
|------------------------------|--------------|---|----|-----|-----|----|
| Transconductance             | $g_{fs}$     | $V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ ,<br>$I_D = 22A$          | 13 | 25  | -   | S  |
| Input capacitance            | $C_{iss}$    | $V_{GS} = 0V$ , $V_{DS} = 25V$ ,<br>$f = 1MHz$                          | -  | 640 | 850 | pF |
| Output capacitance           | $C_{oss}$    |   | -  | 124 | 165 |    |
| Reverse transfer capacitance | $C_{rss}$    |   | -  | 49  | 74  |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD} = 37V$ , $V_{GS} = 10V$ ,<br>$I_D = 22A$ ,<br>$R_G = 9.1\Omega$ | -  | 5   | 7.5 | ns |
| Rise time                    | $t_r$        |   | -  | 22  | 33  |    |
| Turn-off delay time          | $t_{d(off)}$ |   | -  | 33  | 50  |    |
| Fall time                    | $t_f$        |   | -  | 18  | 27  |    |

**Gate Charge Characteristics**

|                       |                 |   |   |     |     |    |
|-----------------------|-----------------|---|---|-----|-----|----|
| Gate to source charge | $Q_{gs}$        | $V_{DD} = 60V$ , $I_D = 22A$                            | - | 2   | 2.7 | nC |
| Gate to drain charge  | $Q_{gd}$        |   | - | 8   | 12  |    |
| Gate charge total     | $Q_g$           | $V_{DD} = 60V$ , $I_D = 22A$ ,<br>$V_{GS} = 0$ to $10V$ | - | 25  | 33  |    |
| Gate plateau voltage  | $V_{(plateau)}$ | $V_{DD} = 60V$ , $I_D = 22A$                            | - | 3.3 | -   | V  |

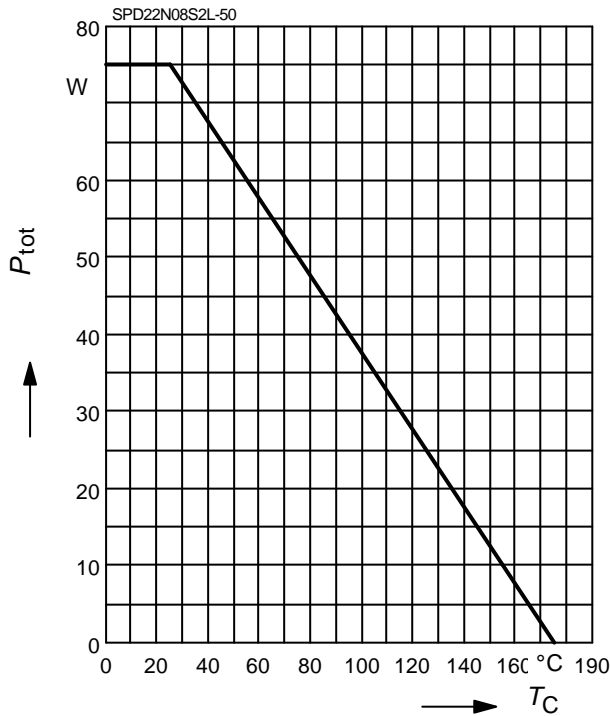
**Reverse Diode**

|  |          |   |   |     |     |    |
|--|----------|---|---|-----|-----|----|
| Inverse diode continuous forward current | $I_S$    | $T_C = 25^\circ C$                                    | - | -   | 25  | A  |
| Inv. diode direct current, pulsed        | $I_{SM}$ |   | - | -   | 100 |    |
| Inverse diode forward voltage            | $V_{SD}$ | $V_{GS} = 0V$ , $I_F = 22A$                           | - | 0.9 | 1.3 | V  |
| Reverse recovery time                    | $t_{rr}$ | $V_R = 40V$ , $I_F = I_S$ ,<br>$di_F/dt = 100A/\mu s$ | - | 44  | 55  | ns |
| Reverse recovery charge                  | $Q_{rr}$ |   | - | 66  | 83  | nC |

### 1 Power dissipation

$$P_{\text{tot}} = f(T_C)$$

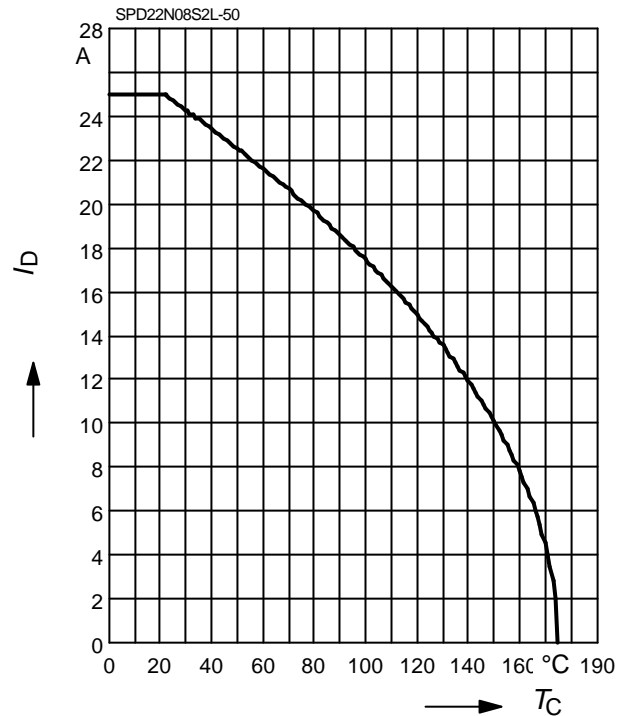
parameter:  $V_{GS} \geq 4 \text{ V}$



### 2 Drain current

$$I_D = f(T_C)$$

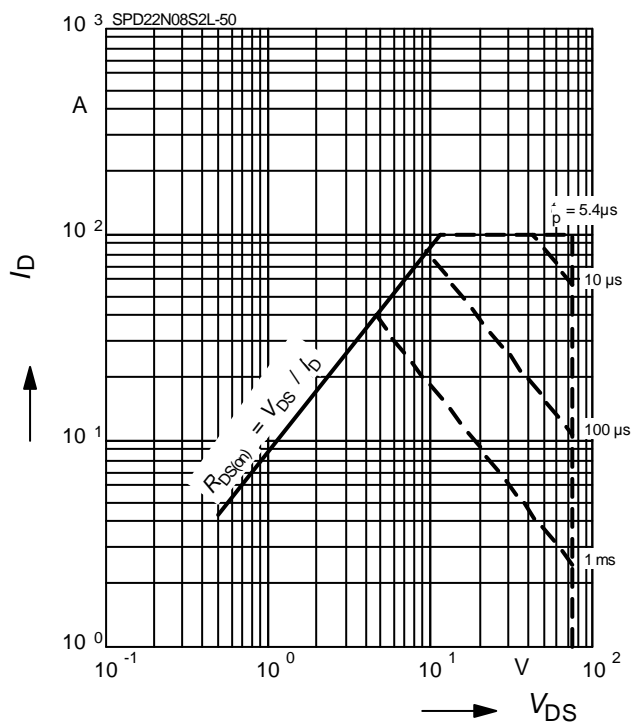
parameter:  $V_{GS} \geq 10 \text{ V}$



### 3 Safe operating area

$$I_D = f(V_{DS})$$

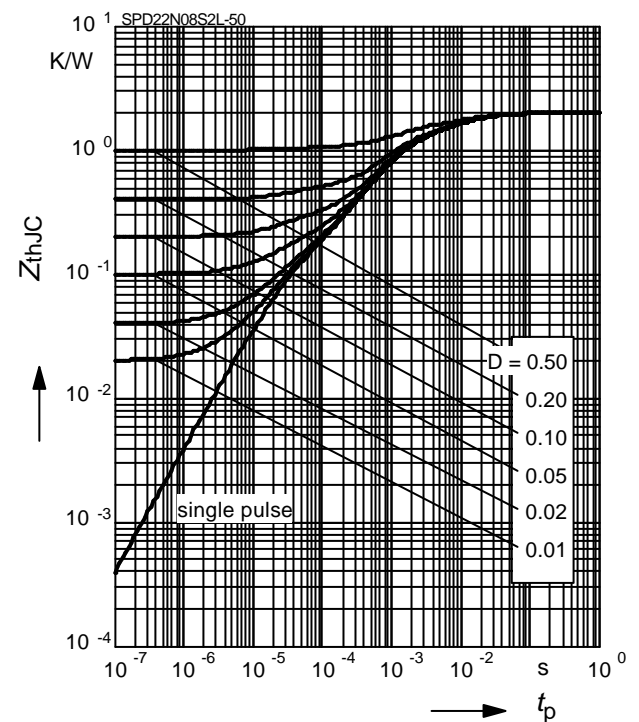
parameter:  $D = 0$ ,  $T_C = 25^\circ\text{C}$



### 4 Max. transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

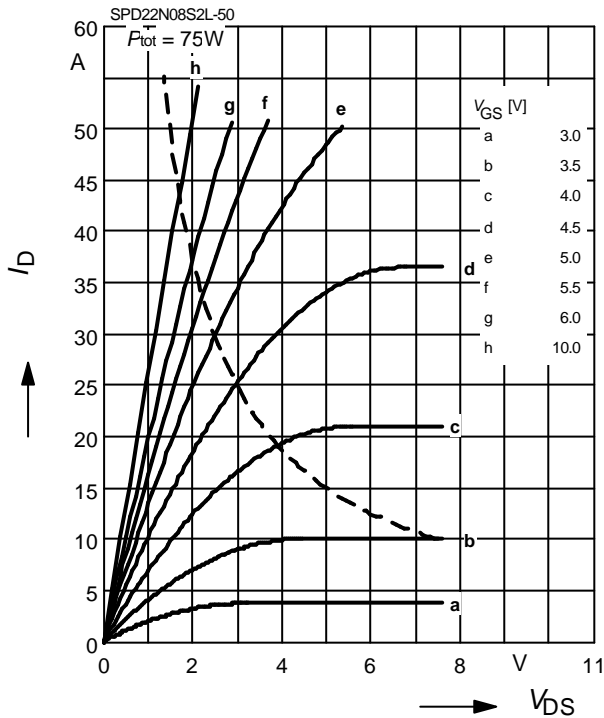
parameter:  $D = t_p/T$



**5 Typ. output characteristic**

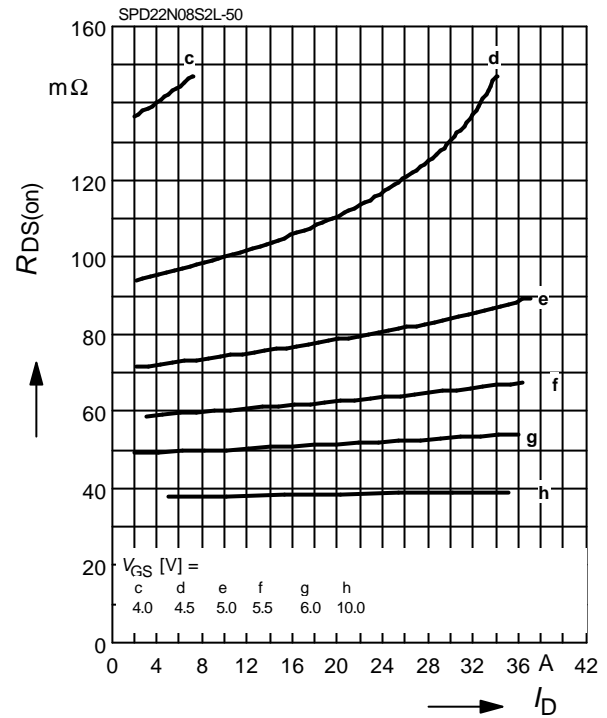
$$I_D = f(V_{DS}); T_J = 25^\circ\text{C}$$

parameter:  $t_p = 80 \mu\text{s}$


**6 Typ. drain-source on resistance**

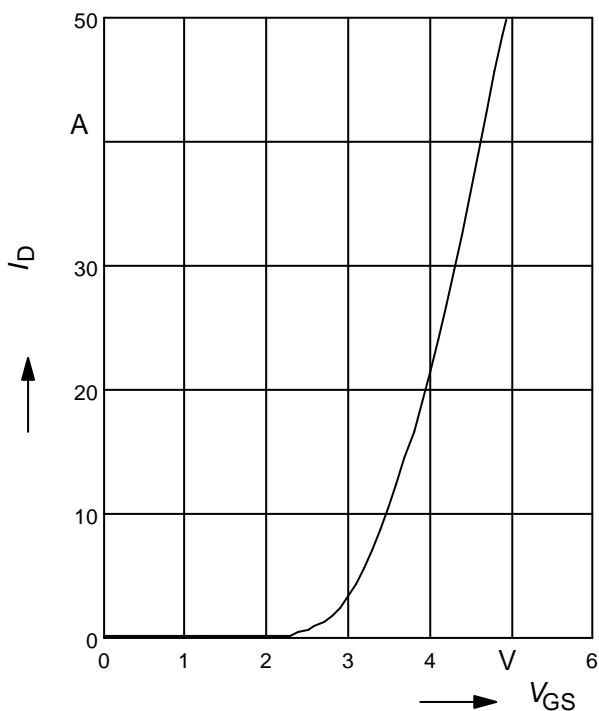
$$R_{DS(on)} = f(I_D)$$

parameter:  $V_{GS}$


**7 Typ. transfer characteristics**

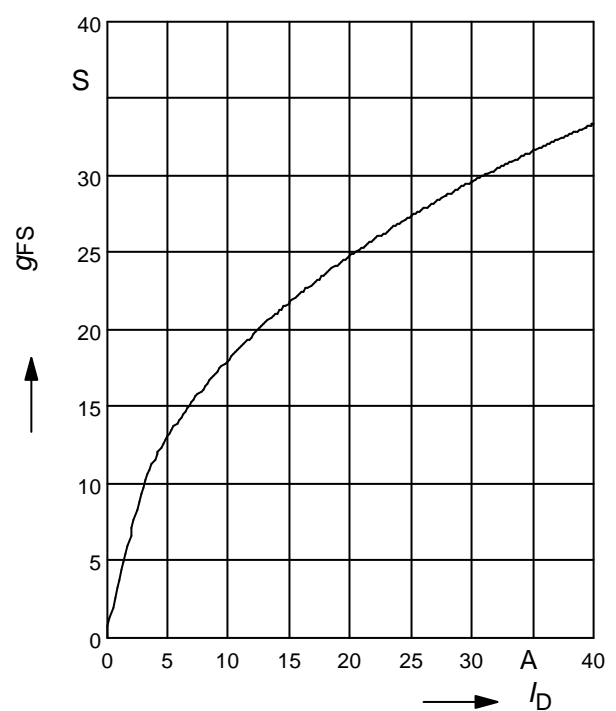
$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

parameter:  $t_p = 80 \mu\text{s}$


**8 Typ. forward transconductance**

$$g_{fs} = f(I_D); T_J = 25^\circ\text{C}$$

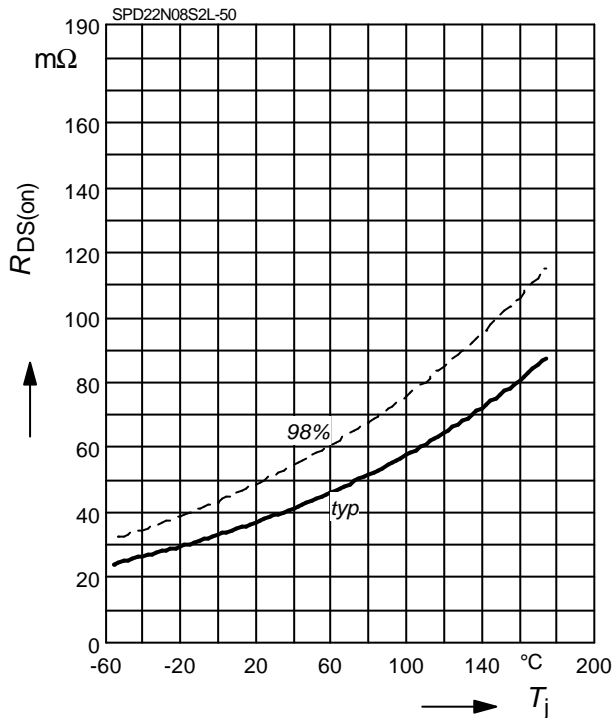
parameter:  $g_{fs}$



**9 Drain-source on-state resistance**

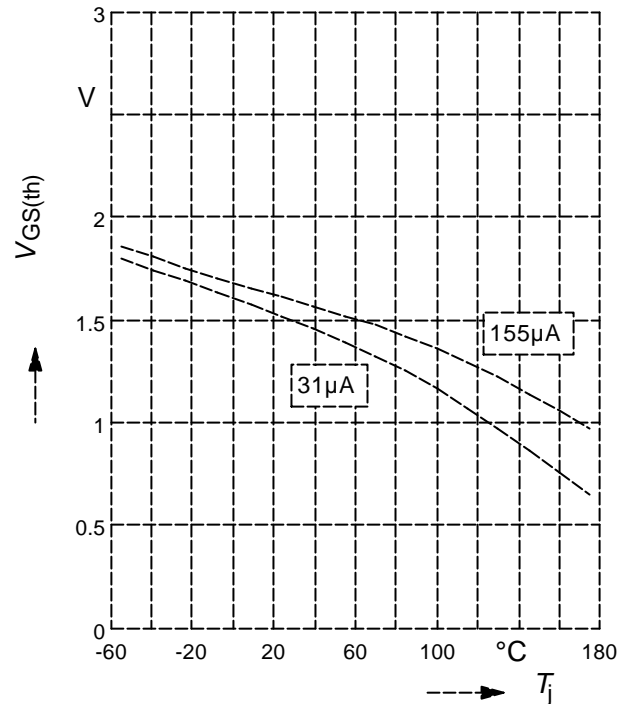
$$R_{DS(on)} = f(T_j)$$

parameter :  $I_D = 11\text{ A}$ ,  $V_{GS} = 10\text{ V}$


**10 Typ. gate threshold voltage**

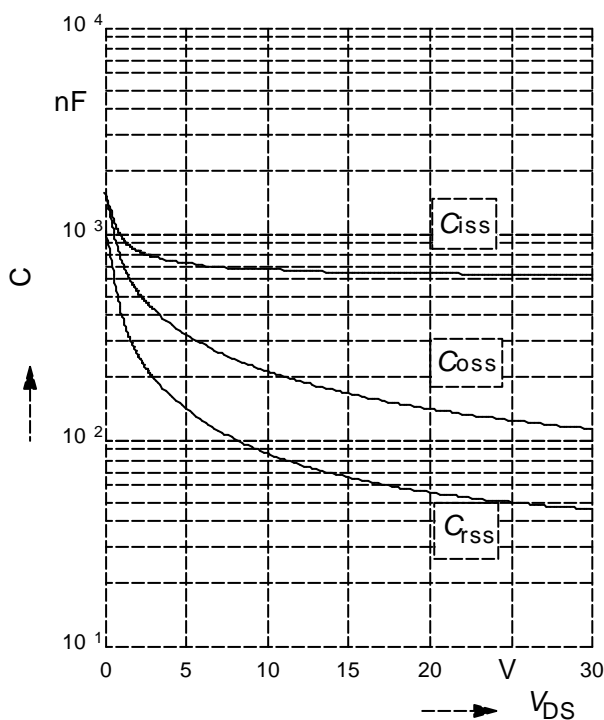
$$V_{GS(th)} = f(T_j)$$

parameter:  $V_{GS} = V_{DS}$


**11 Typ. capacitances**

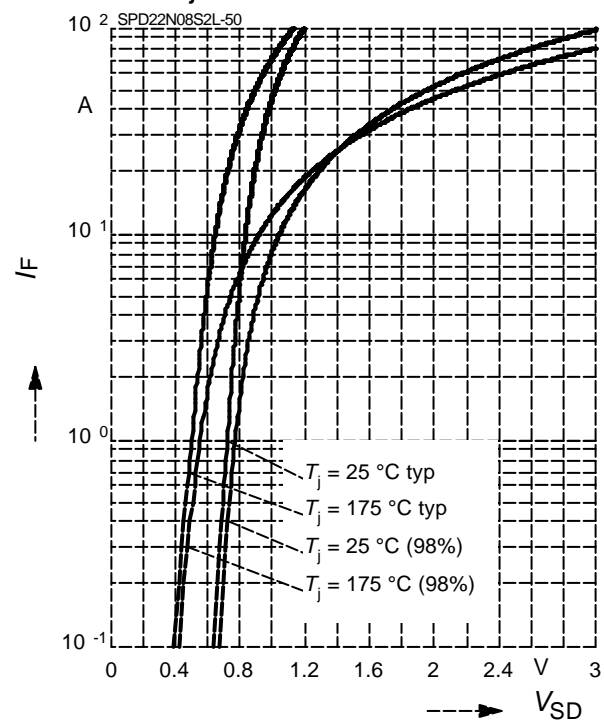
$$C = f(V_{DS})$$

parameter:  $V_{GS}=0\text{V}$ ,  $f=1\text{ MHz}$


**12 Forward character. of reverse diode**

$$I_F = f(V_{SD})$$

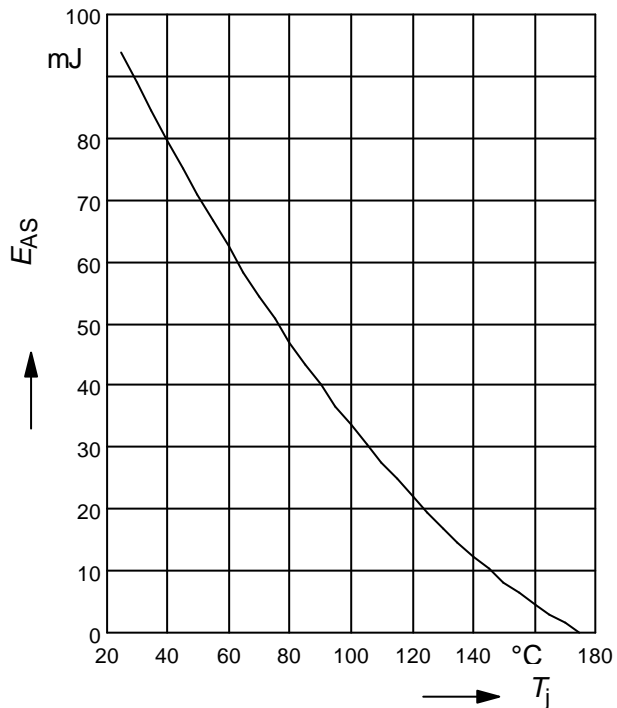
parameter:  $T_j$ ,  $t_p = 80\text{ μs}$



**13 Typ. avalanche energy**

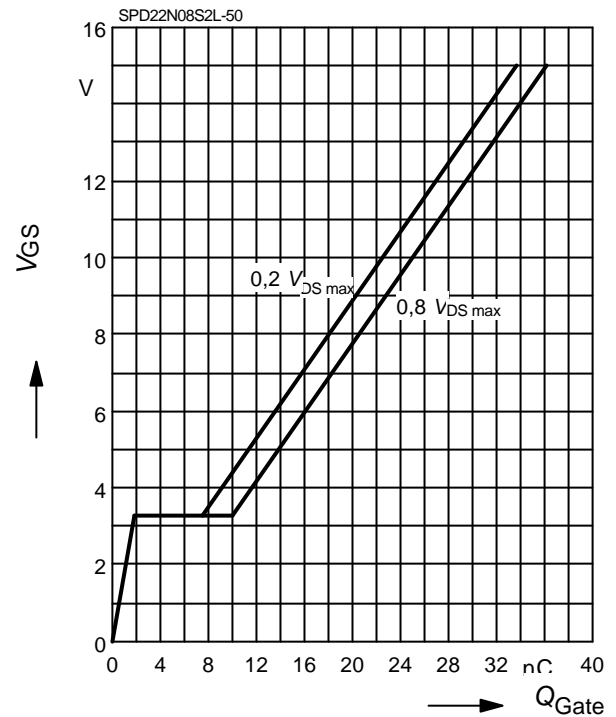
$$E_{AS} = f(T_j)$$

par.:  $I_D = 22\text{A}$ ,  $V_{DD} = 25\text{V}$ ,  $R_{GS} = 25\ \Omega$


**14 Typ. gate charge**

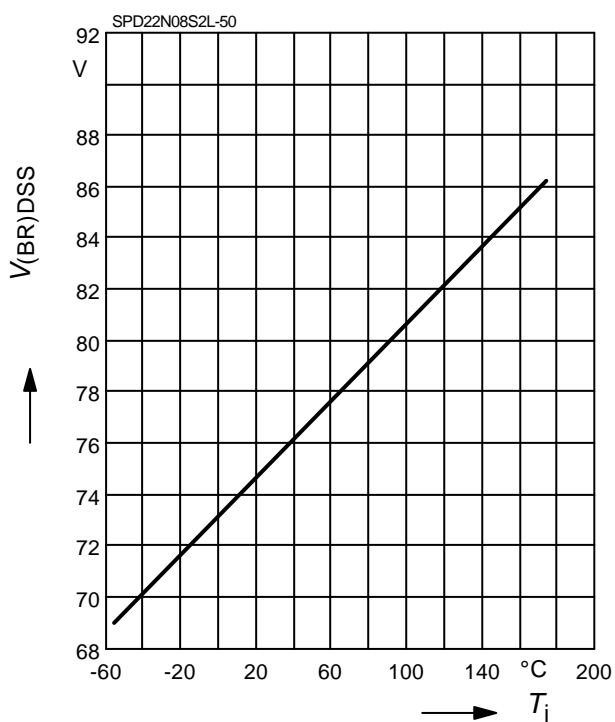
$$V_{GS} = f(Q_{Gate})$$

parameter:  $I_D = 25\text{A}$  pulsed


**15 Drain-source breakdown voltage**

$$V_{(BR)DSS} = f(T_j)$$

parameter:  $I_D = 10\text{mA}$



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**Further information**

Please notice that the part number is BSPD22N08S2L-50, for simplicity the device is referred to by the term SPD22N08S2L-50 throughout this documentation.